# INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)

COHL-3643
Applicant(s)
Andrea Caprara et al.
Filing Date

Docket Number (Optional)

Application Number NEW

Filing Date
HEREWITH (013/2003)

Group Art Unit Unknown

# U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE
w	*AA	5,050,179	09/17/1991	Mooradian	372	44	04/20/1989
OII	*AB	5,131,002	07/14/1992	Mooradian	372	50	02/12/1991
CA)	*AC	5,289,485	02/22/1994	Mooradian	372	45	12/22/1992
Ch.	*AD	5,436,920	07/25/1995	Minemoto et al.	372	21	05/18/1994
w	•AE	5,461,637	10/24/1995	Mooradian et al.	372	92	03/16/1994
64	*AF	5,627,853	05/06/1997	Mooradian et al.	372	92	03/16/1995
<4	*AG	6,285,702	09/04/2001	Caprara, et al.	372	92	03/05/1999

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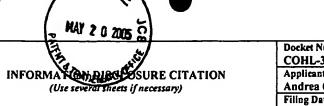
		DOCUMENT					TRA	NSLATION
	REF	NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	YES	No
M	*AH	DE 25 22 338 A1	12/04/1975	Germany	H01S	3/10	~	X
CN	*AI	WO 93/14542 A1	07/22/1993	PCT	HOIS	3/109		نـــــــــــ
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al	*AO	J.V. Sandusky et al., "A CW External-Cavity Surface-Emitting Laser," IEEE Photonics Technology Letters, Vol. 8, No. 3,
100		March 1996, pp. 313-315.
1	*AP	M. Kuznetsov et al., "High-Power (x0.5-W CW) Diode-Pumped Vertical-External-Cavity Surface-Emitting Semiconductor
-pt	<u> </u>	Lasers with Circular TEM <sub>∞</sub> Beams," IEEE Photonics Technology Letters, Vol. 9, No. 8, August 1997, pp. 1063-1065.
in	*AQ	A. Rosiewicz et al., "Optical pumping improves VCSEL performance," Laser Focus World, June 1997, pp. 133-136.
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M.	į	laser," Advanced Solid State Laser Conference, Sandia National Laboratories, SAND-98-2108C, CONF-990105,
7	_i	December 31, 1998, 5 pages in length.
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dur		Letters, Vol. 16, No. 18, September 15, 1991, pp. 1394-1396.
	*AT	PCT International Search Report, mailed February 25, 2000, for International Application No. PCT/US99/24303, filed
ley	1	October 18, 1999, 7 pages in length.

Examiner	sluy	Date Considered 8/16/65
Examiner:	Initial if citation considered, whether or not citation is	s in conformance with MPEP Section 609; Draw line through citation if
not in confo	rmance and not considered. Include copy of this form	n with next communication to applicant.



Docket Number (Optional) COHL-3643	Application Number 10/695,583		
Applicant(s) Andrea Caprara et al.			
Filing Date October 28, 2003	Group Art Unit		

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	*AC	5,289,485	02/22/1994	Mooradian	372	45 ·	12/22/1992
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+ See "AV" Search Report below

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l ~	AP	J.V. Sandusky et al., "A CW External-Cavity Surface-Emitting Laser," IEEE Photonics Technology Letters, Vol. 8, No. 3,
		March 1996, pp. 313-315.
	AQ	M. Kuznetsov et al., "High-Power (>0.5-W CW) Diode-Pumped Vertical-External-Cavity Surface-Emitting Semiconductor
		Lasers with Circular TEM <sub>00</sub> Beams," IEEE Photonics Technology Letters, Vol. 9, No. 8, August 1997, pp. 1063-1065.
	AR	A. Rosiewicz et al., "Optical pumping improves VCSEL performance," Laser Focus World, June 1997, pp. 133-136.
	AS	W.J. Alford et al., "Intracavity frequency doubling of an optically-pumped, external-cavity surface-emitting semiconductor
		laser," Advanced Solid State Laser Conference, Sandia National Laboratories, SAND-98-2108C, CONF-990105,
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	Examiner Sulver	Date Considered \(\frac{\gamma\left(\beta/c\)}{\left(\beta/c)}\)
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1	not in conformance and not considered. Include copy of this form with	next communication to applicant.